

2SK2118

Silicon N Channel MOS FET

Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No Secondary Breakdown
- Suitable for Switching regulator, DC – DC converter, Motor Control

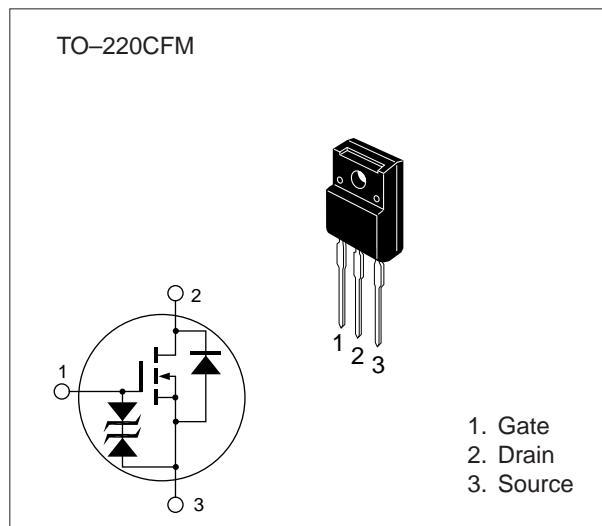


Table 1 Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	600	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D	5	A
Drain peak current	I _{D(pulse)} *	20	A
Body-drain diode reverse drain current	I _{DR}	5	A
Channel dissipation	P _{ch} **	35	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* PW ≤ 10 µs, duty cycle ≤ 1 %

** Value at T_c = 25 °C

Table 2 Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	V _{(BR)DSS}	600	—	—	V	I _D = 10 mA, V _{GS} = 0
Gate to source breakdown voltage	V _{(BR)GSS}	±30	—	—	V	I _G = ±100 µA, V _{DS} = 0
Gate to source leak current	I _{GSS}	—	—	±10	µA	V _{GS} = ±25 V, V _{DS} = 0
Zero gate voltage drain current	I _{DSS}	—	—	250	µA	V _{DS} = 500 V, V _{GS} = 0
Gate to source cutoff voltage	V _{GS(off)}	2.0	—	3.0	V	I _D = 1 mA, V _{DS} = 10 V
Static drain to source on state resistance	R _{DS(on)}	—	1.1	1.5	Ω	I _D = 2.5 A V _{GS} = 10 V *
Forward transfer admittance	y _{fs}	3.0	5.0	—	S	I _D = 2.5 A V _{DS} = 10 V *
Input capacitance	C _{iss}	—	1000	—	pF	V _{DS} = 10 V
Output capacitance	C _{oss}	—	250	—	pF	V _{GS} = 0
Reverse transfer capacitance	C _{rss}	—	45	—	pF	f = 1 MHz
Turn-on delay time	t _{d(on)}	—	12	—	ns	I _D = 2.5 A
Rise time	t _r	—	45	—	ns	V _{GS} = 10 V
Turn-off delay time	t _{d(off)}	—	105	—	ns	R _L = 12Ω
Fall time	t _f	—	55	—	ns	
Body-drain diode forward voltage	V _{DF}	—	0.9	—	V	I _F = 5 A, V _{GS} = 0
Body-drain diode reverse recovery time	t _{rr}	—	500	—	ns	I _F = 5 A, V _{GS} = 0, dI _F / dt = 100 A / µs

* Pulse Test

■ See characteristic curve of 2SK1404.

